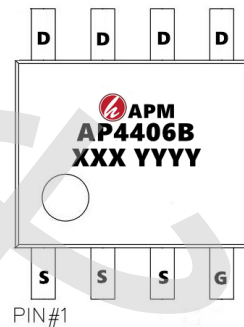
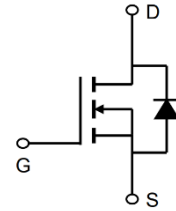


30V N-Channel Enhancement Mode MOSFET

Description

The AP4406B uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = 30V$ $I_D = 10A$

$R_{DS(ON)} < 25m\Omega$ @ $V_{GS} = 10V$

Application

Battery protection

Load switch

Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP4406B	SOP-8	AP4406B XXX YYYY	3000

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	30	V
VGS	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	10	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6.2	A
IDM	Pulsed Drain Current ²	30	A
EAS	Single Pulse Avalanche Energy ³	8	mJ
IAS	Avalanche Current	12.7	A
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ⁴	1.5	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	25	$^\circ C/W$

30V N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	32	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.023	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =10A	---	15.6	25	mΩ
		V _{GS} =4.5V, I _D =8A	---	28.5	38	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.6	2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	-4.2	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V, I _D =10A	---	5.5	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.3	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =10A	---	4.9	---	nC
Q _{gs}	Gate-Source Charge		---	1.66	---	
Q _{gd}	Gate-Drain Charge		---	1.85	---	
Td(on)	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω, I _D =10A	---	1.6	---	ns
T _r	Rise Time		---	15.8	---	
Td(off)	Turn-Off Delay Time		---	13	---	
T _f	Fall Time		---	4.8	---	
Ciss	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	216	---	pF
Coss	Output Capacitance		---	62	---	
Crss	Reverse Transfer Capacitance		---	51	---	
IS	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	24	A
ISM	Pulsed Source Current ^{2,5}		---	---	50	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
trr	Reverse Recovery Time	IF=10A, dI/dt=100A/μs, T _J =25°C	---	8.7	---	nS
Q _{rr}	Reverse Recovery Charge		---	1.95	---	nC

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

30V N-Channel Enhancement Mode MOSFET

Typical Characteristics

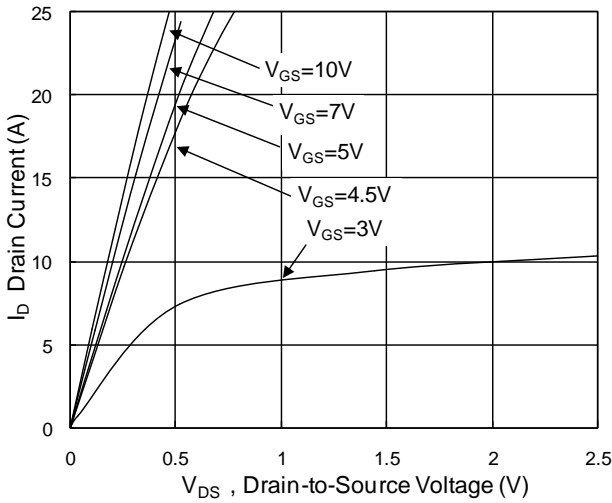


Fig.1 Typical Output Characteristics

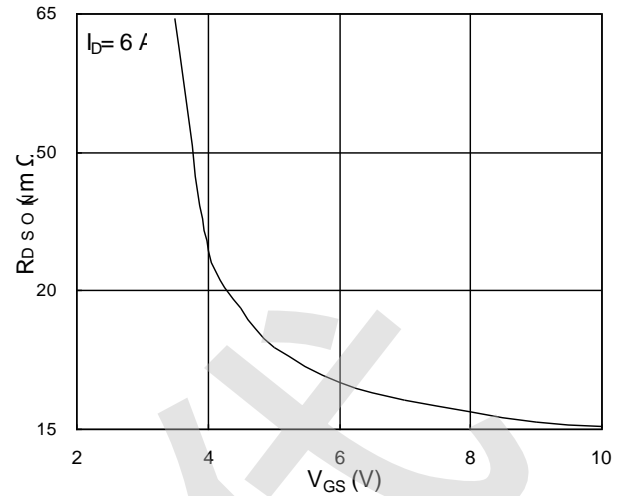


Fig.2 On-Resistance vs. Gate-Source

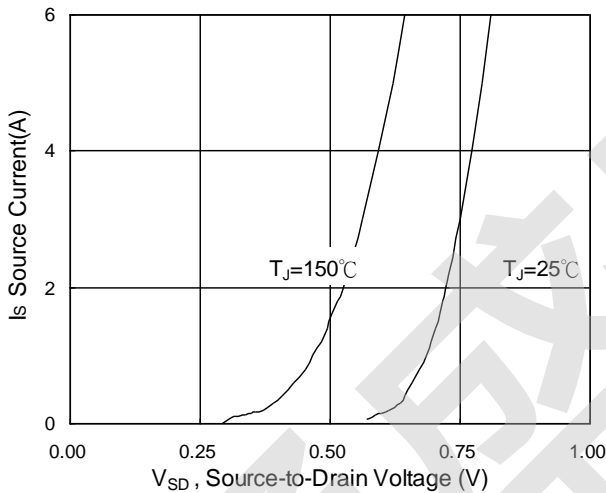


Fig.3 Forward Characteristics Of Reverse

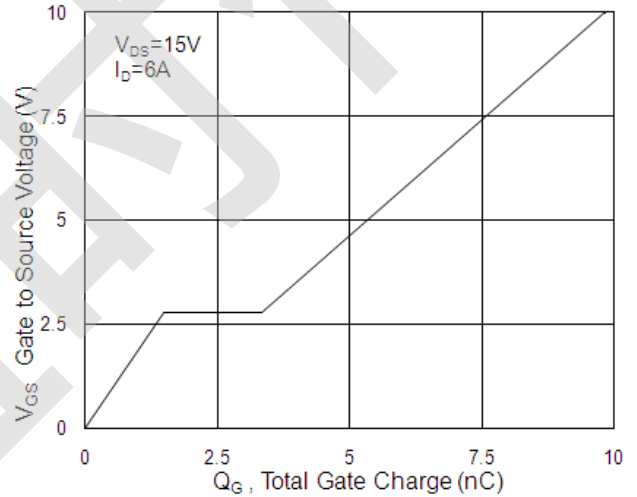


Fig.4 Gate-Charge Characteristics

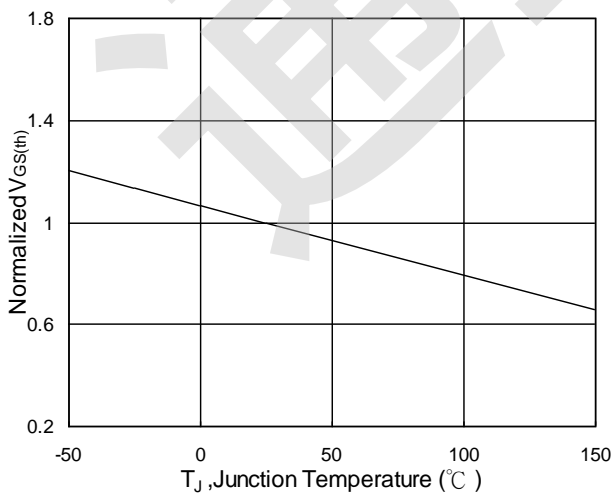


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

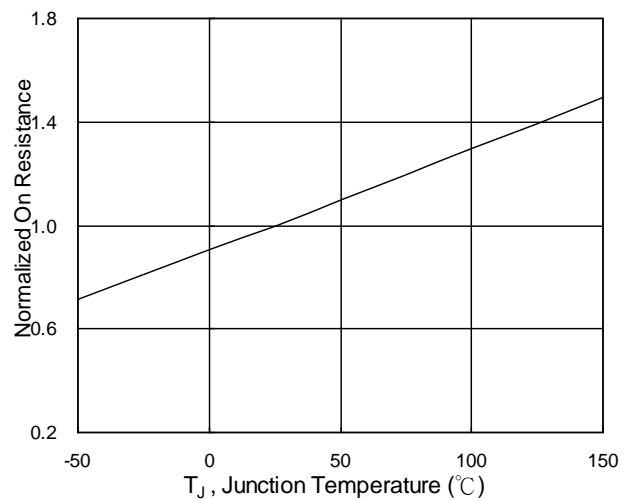


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

30V N-Channel Enhancement Mode MOSFET

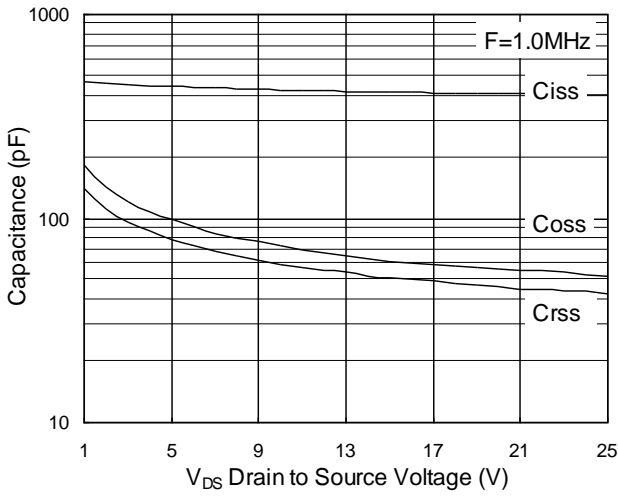


Fig.7 Capacitance

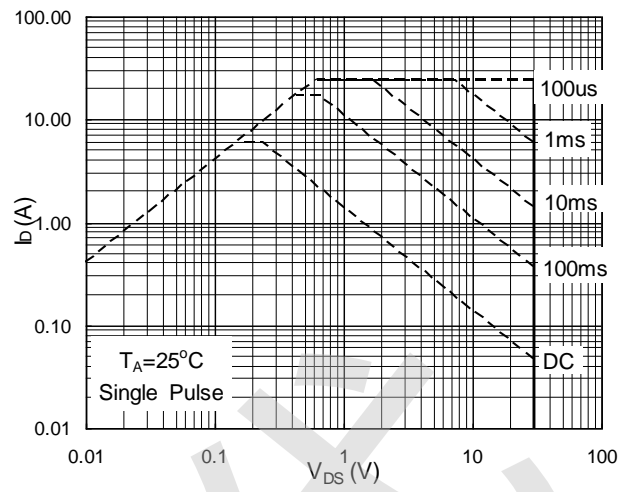


Fig.8 Safe Operating Area

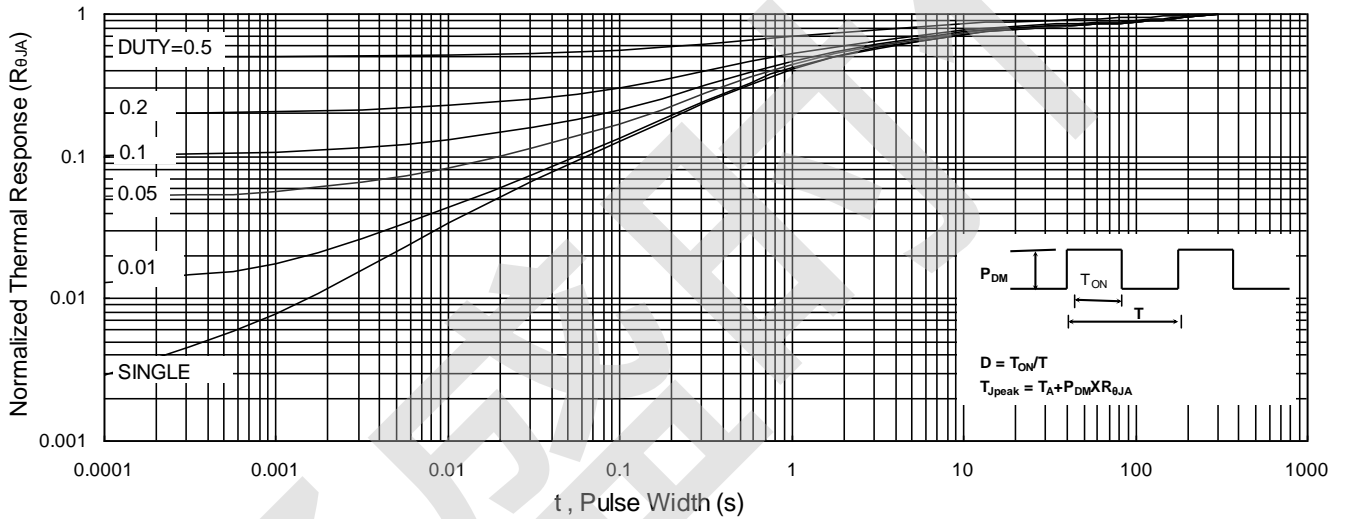


Fig.9 Normalized Maximum Transient Thermal Impedance

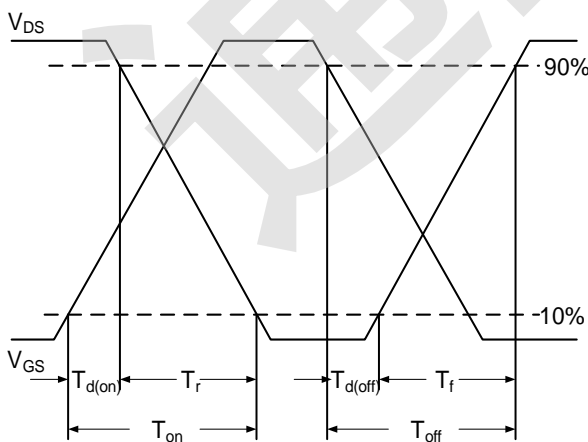


Fig.10 Switching Time Waveform

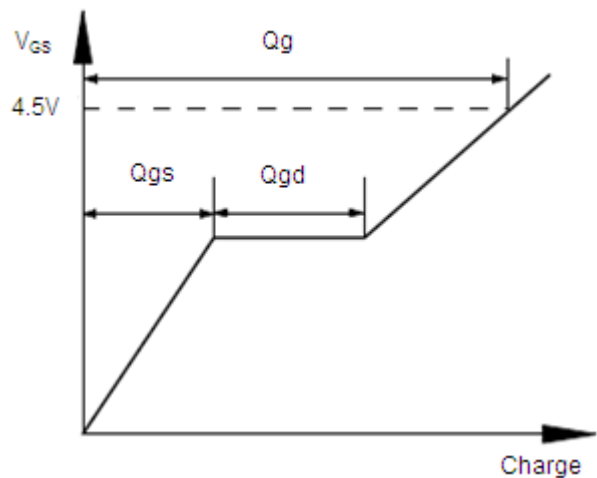
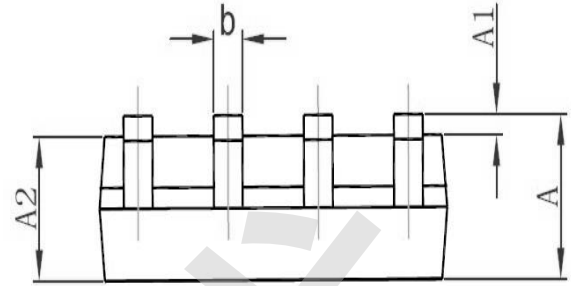
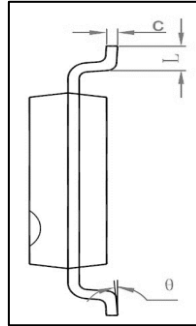
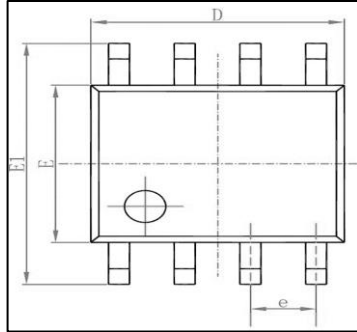
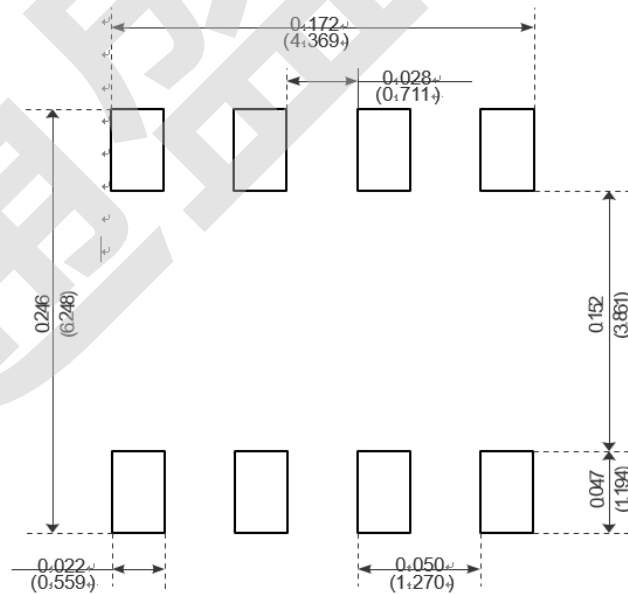


Fig.11 Gate Charge Waveform

Package Mechanical Data-SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads

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30V N-Channel Enhancement Mode MOSFET

Edition	Date	Change
Rve1.0	2020/1/01	Initial release

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